

ABSTRACT OF THE DISCLOSURE

An AlCu alloy interconnect line (100) including a TiN barrier layer (110), a lower Ti metal layer (120), an AlCu layer (130) and a TiN cap layer (140) is formed on a plasma oxide film formed on a semiconductor substrate in which devices are formed. Heat treatment is conducted to cause Al contained in the AlCu layer (130) and Ti contained in the lower Ti metal layer (120) to react with each other, thereby forming a lower AlTi alloy layer (150) in a lower portion of the AlCu layer (130). A via hole (170) is thereafter formed. A current path extending from the via hole (170) to reach the lower AlTi alloy layer (150) is ensured without passing through the AlCu layer (130), allowing electromigration resistance to be improved.